





FZT789A

25V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -25V
- I_C = -3A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < -250mV @ -1A
- $R_{CE(sat)} = 93m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified up to -6A for a High Gain Hold-Up
- Complementary NPN Type: FZT689B
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.112 grams (Approximate)

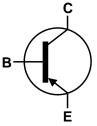
Applications

- Power MOSFET & IGBT Gate Driving
- Battery Powered Circuits
- Fast Charge Converters
- Low Loss Power Switching

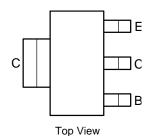
SOT223



Top View



Device Symbol



Pin-Out

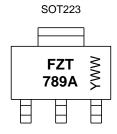
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT789ATA	AEC-Q101	FZT789A	7	12	1,000
FZT789AQTA	Automotive	FZT789A	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information



FZT 789A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	lc	-3	А
Peak Pulse Current	I _{CM}	-6	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		3.0		
Rower Dissipation	(Note 7)	D-	2.0	W	
Power Dissipation	(Note 8)	P _D	1.6		
	(Note 9)		1.2		
	(Note 6)		41.7		
Thermal Resistance, Junction to Ambient	(Note 7)	_	62.5		
Thermal Resistance, Junction to Ambient	(Note 8)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 9)		104	1	
Thermal Resistance Junction to Lead	(Note 10)	$R_{ hetaJL}$	12.9		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 11)

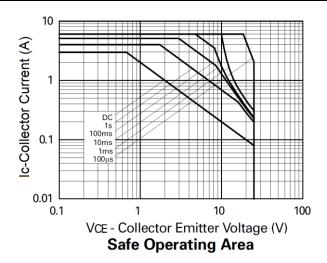
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

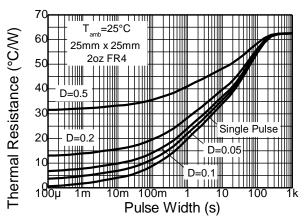
Notes:

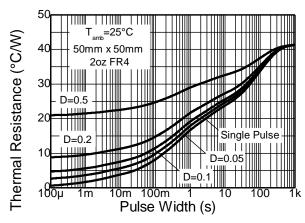
- 6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
- 8. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 9. Same as Note 6, except the device is mounted on minimum recommended pad layout.
- 10. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information

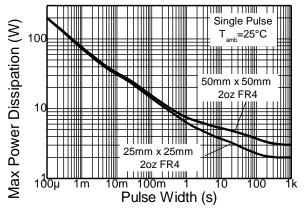


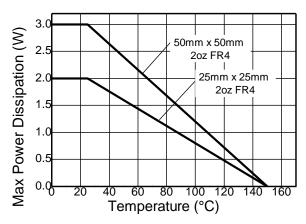




Transient Thermal Impedance

Transient Thermal Impedance





Pulse Power Dissipation





FZT789A

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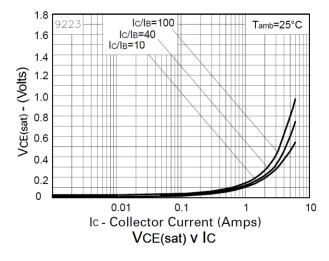
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

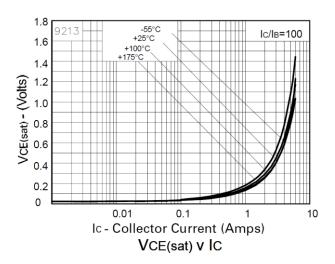
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-30	-40	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	-25	-35	-	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.5	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I _{CBO}	-	<1	-100	nA	V _{CB} = -15V
Collector Cut-Oil Current		-	=	-10	μΑ	$V_{CB} = -15V, T_{amb} = +100$ °C
Collector Cut-Off Current	I _{CES}	-	<1	-100	nA	V _{CE} = -15V
Emitter Cut-Off Current	I _{EBO}	_	<1	-100	nA	$V_{EB} = -5.6V$
		_	-0.15	-0.25		$I_C = -1A$, $I_B = -10mA$
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}		-0.30	-0.45	V	$I_C = -2A$, $I_B = -20mA$
		_	-0.30	-0.50		$I_C = -3A$, $I_B = -100mA$
Base-Emitter Saturation Voltage (Note 12)	$V_{BE(sat)}$	_	-0.80	-1.0	V	$I_C = -1A$, $I_B = -10mA$
Base-Emitter Turn-On Voltage (Note 12)	$V_{BE(on)}$	_	-0.75	-1.1	V	$I_C = -1A$, $V_{CE} = -2V$
		300	-	800		$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 12)	h _{FE}	250	-	-		$I_C = -1A$, $V_{CE} = -2V$
DC Current Gain (Note 12)		200	-	-	_	$I_C = -2A$, $V_{CE} = -2V$
		100	-	=		$I_C = -6A$, $V_{CE} = -2V$
Current Gain-Bandwidth Product	f⊤	100	-	I	MHz	$V_{CE} = -5V$, $I_{C} = -50$ mA f = 50MHz
Turn-On Time	t _{on}	-	35	-	ns	$V_{CC} = -10V, I_{C} = -500mA$
Turn-Off Time	t _{off}	-	400	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$
Input Capacitance	C_{ibo}	-	225	-	pF	$V_{EB} = -0.5V$, $f = 1MHz$
Output Capacitance	C_obo	_	25	_	pF	$V_{CB} = -10V$, $f = 1MHz$

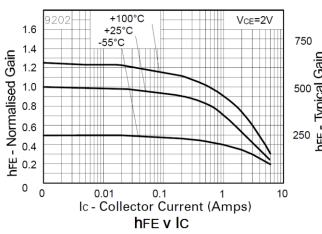
Note: 12. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

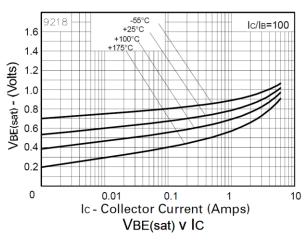


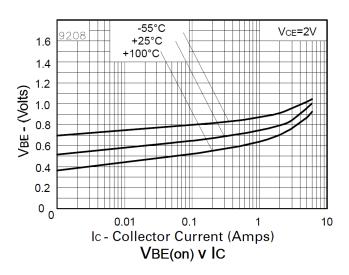
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







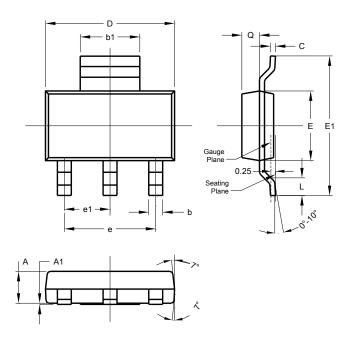






Package Outline Dimensions

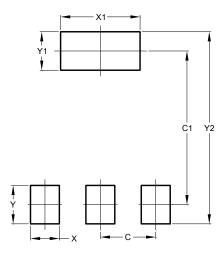
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00





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